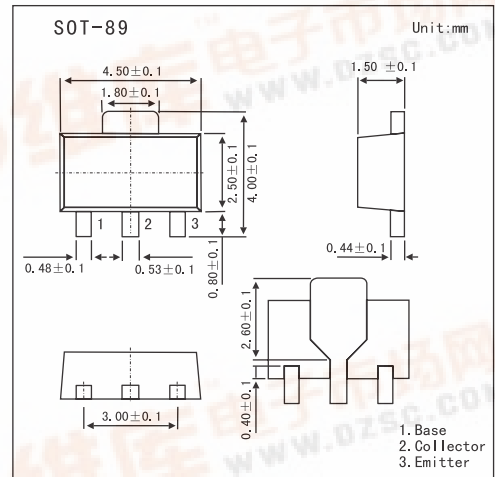


SMD Type Transistors

PNP Silicon Epitaxial Transistor
2SB804

Features

- World standard miniature package:SOT-89
- High collector to base voltage: $V_{CB0} > -100V$
- Excellent DC current gain linearity.



Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CB0}	-100	V
Collector to emitter voltage	V_{CEO}	-80	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	mA
Collector current(Pulse) *	I_C	-1.5	mA
Total power dissipation	P_T	2	W
Junction temperature	T_j	150	$^{\circ}C$
Storage temperature range	T_{stg}	-55 to +150	$^{\circ}C$

* $PW \leq 10ms, duty\ cycle \leq 50\%$.

Electrical Characteristics $T_a = 25^{\circ}C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -100V, I_E = 0$			-100	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5.0V, I_C = 0$			-100	nA
DC current gain *	h_{FE}	$V_{CE} = -2.0V, I_C = -100mA$	90	200	400	
		$V_{CE} = -2.0V, I_C = -500mA$	25	80		
Collector saturation voltage *	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.29	-0.5	V
Base saturation voltage *	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.9	-1.5	V
Base-emitter voltage *	V_{BE}	$V_{CE} = -10V, I_C = -10mA$	-600	-640	-700	mV
Gain bandwidth product	f_T	$V_{CE} = -5.0V, I_E = 10mA$		80		MHz
Output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1.0MHz$		26		pF

* Pulsed: $PW \leq 350\mu s, duty\ cycle \leq 2\%$

hFE Classification

Marking	AW	AV	AU
hFE	90~180	135~270	200~400

